EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S234	701	S230 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S233	397	S229 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S232	286	(vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM memory adj cell) and capacitor).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S231	74	((SGT! surround$3 adj gate) and (DRAM memory adj cell)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S230	839	S228 and (epitaxial$2 epitaxy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S229	517	S227 and (epitaxial$2 epitaxy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S228	1818	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM memory adj cell) and capacitor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S227	1227	(SGT! surround$3 adj gate) and (DRAM memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S226	43	S225 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44

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S20 7	307	S206 and (epitaxial$2 epitaxy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:44
S10 0	889	(SGT surround$3 adj gate) and (DRAM memory adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:38
S22 5	45	(vertical adj replacement adj gate) and (memory DRAM RAM SRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:29
S22 4	179	S222 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:29
S22 2	207	(vertical adj replacement adj gate VRG!) and (memory DRAM RAM SRAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:29
S22 3	0	((vertical adj replacement adj gate VRG!) and (memory DRAM RAM SRAM)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:28
S11 4	601	S101 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:28
S12 1	455	S120 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:27
S12 5	1502	vertical adj (FET MOSFET transistor channel) and (DRAM dynamic adj RAM)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:25
S22 1	2	(leslie near3 terrence).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:21

S220	1033	(257/E27.086).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 09:21
S189	736	S187 and (@ad<"20040127" @rlad<"20040127")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/07 09:21
S219	715	(257/E29.262).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 09:20
S218	901	(257/329).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 09:20
S217	867	(257/300).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/07 09:20